

UNISONIC TECHNOLOGIES CO., LTD

2N7002T

Power MOSFET

300mA, 60V N-CHANNEL POWER MOSFET

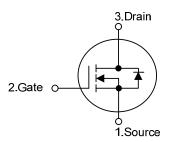
DESCRIPTION

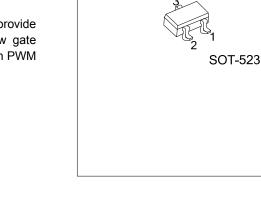
The UTC **2N7002T** uses advanced technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

FEATURES

- * High Density Cell Design for Low R_{DS(ON)}.
- * Voltage Controlled Small Signal Switch
- * Rugged and Reliable
- * High Saturation Current Capability







ORDERING INFORMATION

| Ordering Number | | Package | | Pin Assignment | | | Deaking | |
|--|-----------------------------------|---------|-----------------------|--------------------|------------|--------|-----------|--|
| | | | | 1 | 2 | 3 | Packing | |
| 2N7002TG-AN3-R | | SOT-523 | | S | G | D | Tape Reel | |
| Note: Pin Assignment: G: Gate D: Drain S: Source | | | | | | | | |
| 2N7002T <u>G-AN3-</u> R | (1)Packing Type (2)Package Typ | | (1) R: Ta (2) AN3: | pe Reel SOT-523 | | | | |
| | —— (3)Green Packa | ge | (3) G: Ha | alogen Free | e and Lead | l Free | | |

MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified.)

| PARAMETER | | SYMBOL | RATINGS | UNIT |
|---|-------------------------|------------------|------------|-------|
| Drain-Source Voltage | | V _{DSS} | 60 | V |
| Drain-Gate Voltage (R _{GS} ≤1MΩ) | | V _{DGR} | 60 | V |
| Gate Source Voltage | Continuous | N/ | ±20 | V |
| | Non Repetitive(tp<50µs) | V _{GSS} | ±40 | v |
| Drain Current | Continuous | I _D | 300 | m ^ |
| | Pulsed | | 800 | - mA |
| Power Dissipation | Power Dissipation | | 200 | mW |
| Derated Above 25°C | | PD | 1.6 | mW/°C |
| Junction Temperature | | TJ | + 150 | °C |
| Storage Temperature | | T _{STG} | -55 ~ +150 | °C |

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

THERMAL DATA

| PARAMETER | SYMBOL | RATINGS | UNIT | |
|---------------------|-----------------|-------------|------|--|
| Junction to Ambient | θ _{JA} | 625 (Note1) | °C/W | |

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|------------------------------------|--|--|-----|------|------|------|
| OFF CHARACTERISTICS | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V, I _D =10µA | 60 | | | V |
| Drain-Source Leakage Current | I _{DSS} | V _{DS} =60V, V _{GS} =0V | | | 1 | μA |
| Cata Source Leakage Current | I _{GSSF} | V _{GS} =20V, V _{DS} =0V | | | 100 | nA |
| Gate-Source Leakage Current | I _{GSSR} V _{GS} =-20V, V _{DS} =0V | | | | -100 | nA |
| ON CHARACTERISTICS (Note2) | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | $V_{GS} = V_{DS}, I_{D} = 250 \mu A$ | 1 | 2.1 | 2.5 | V |
| Drain-Source On-Voltage | V _{DS (ON)} | V _{GS} = 10V, I _D =300mA | | 0.6 | 3.75 | v |
| | | V _{GS} = 5.0V, I _D =50mA | | 0.09 | 1.5 | v |
| Otatia Dasia Osuma Os Dasistanas | R _{DS (ON)} | V _{GS} =10V, I _D =300mA | | | 13.5 | Ω |
| Static Drain-Source On-Resistance | | V _{GS} =5.0V, I _D =50mA | | | 7.5 | Ω |
| DYNAMIC CHARACTERISTICS | | | | | | |
| Input Capacitance | CISS | V _{DS} =25V,V _{GS} =0V, f=1.0MHz | | 20 | 50 | pF |
| Output Capacitance | Coss | | | 11 | 25 | pF |
| Reverse Transfer Capacitance | C _{RSS} | | | 4 | 5 | pF |
| Turn-On Time | ton | V _{DD} =30V, R _L =150Ω, I _D =200mA, | | | 20 | nS |
| | | V_{GS} =10V, R_{GEN} =25 Ω | | | | |
| Turn-Off Time | toff | V _{DD} =30V, R _L =25Ω, I _D =200mA, | | | 20 | nS |
| | | V_{GS} =10V, R_{GEN} =25 Ω | | 20 | | 113 |
| DRAIN-SOURCE DIODE CHARACTEI | RISTICS AN | D MAXIMUM RATINGS | | | | |
| Drain-Source Diode Forward Voltage | V_{SD} | V _{GS} =0V, I _S =300mA (Note) | | 0.88 | 1.5 | V |
| Maximum Pulsed Drain-Source Diode | | | | | 0.8 | А |
| Forward Current | I _{SM} | | | | 0.0 | A |
| Maximum Continuous Drain-Source | ls | | | | 300 | mA |
| Diode Forward Current | 15 | | | | 300 | |

Notes: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch. Minimum land pad size.

2. Pulse Test: Pulse Width≤300µs, Duty Cycle≤2.0%



■ TEST CIRCUIT AND WAVEFORM

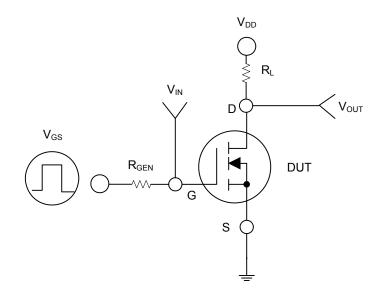


Fig. 1

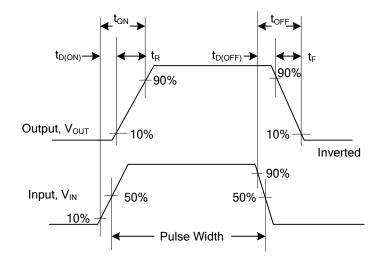


Fig. 2 Switching Waveforms

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